

# BAS32L

## Silicon Epitaxial Planar Switching Diode

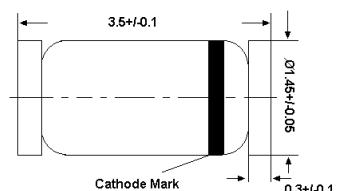
### Features

- Small hermetically-sealed glass SMD package
- High switching speed

### Application

- High-speed switching
- Fast logic applications

LL-34



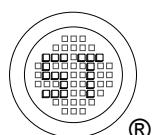
Glass case MiniMELF  
Dimensions in mm

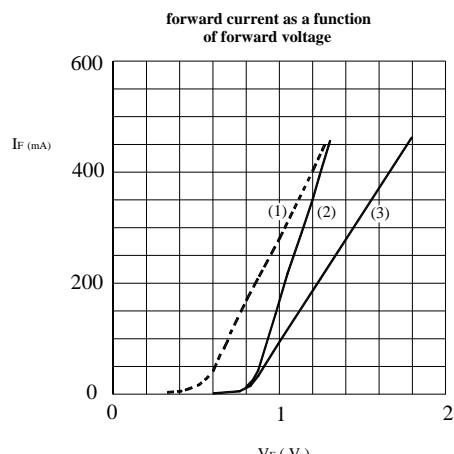
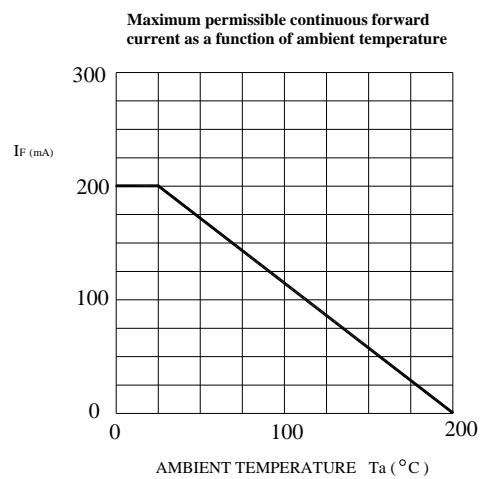
### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

| Parameter  | Symbol    | Value         | Unit |
|--|-----------|---------------|------|
| Repetitive Peak Reverse Voltage  | $V_{RRM}$ | 75            | V    |
| Continuous Reverse Voltage   | $V_R$     | 75            | V    |
| Continuous Forward Current   | $I_F$     | 200           | mA   |
| Repetitive Peak Forward Current  | $I_{FRM}$ | 450           | mA   |
| Non-repetitive Peak Forward Surge Current<br>at $t = 1 \text{ s}$<br>at $t = 1 \text{ ms}$<br>at $t = 1 \mu\text{s}$ | $I_{FSM}$ | 0.5<br>1<br>4 | A    |
| Power dissipation  | $P_{tot}$ | 500           | mW   |
| Junction temperature   | $T_j$     | 175           | °C   |
| Storage temperature range  | $T_{stg}$ | - 65 to + 175 | °C   |

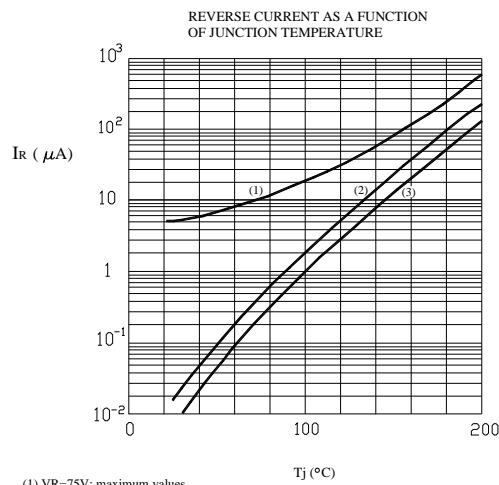
### Characteristics at $T_a = 25^\circ\text{C}$

| Parameter   | Symbol                           | Min.             | Max.                 | Unit                 |
|---|----------------------------------|------------------|----------------------|----------------------|
| Forward Voltage<br>at $I_F = 5 \text{ mA}$<br>at $I_F = 100 \text{ mA}$<br>at $I_F = 100 \text{ mA}, T_j = 100^\circ\text{C}$   | $V_F$<br>$V_F$<br>$V_F$          | 620<br>-<br>-    | 750<br>1000<br>930   | mV<br>mV<br>mV       |
| Reverse Current<br>at $V_R = 20 \text{ V}$<br>at $V_R = 75 \text{ V}$<br>at $V_R = 20 \text{ V}, T_j = 150^\circ\text{C}$<br>at $V_R = 75 \text{ V}, T_j = 150^\circ\text{C}$ | $I_R$<br>$I_R$<br>$I_R$<br>$I_R$ | -<br>-<br>-<br>- | 25<br>5<br>50<br>100 | nA<br>μA<br>μA<br>μA |
| Reverse Breakdown Voltage<br>at $I_R = 100 \mu\text{A}$   | $V_{(BR)R}$                      | 100              | -                    | V                    |
| Diode Capacitance<br>at $V_R = 0, f = 1 \text{ MHz}$  | $C_d$                            | -                | 2                    | pF                   |
| Reverse Recovery Time<br>at $I_F = 10 \text{ mA}$ to $I_R = 1 \text{ mA}, V_R = 6 \text{ V}, R_L = 100 \Omega$  | $t_{rr}$                         | -                | 4                    | ns                   |

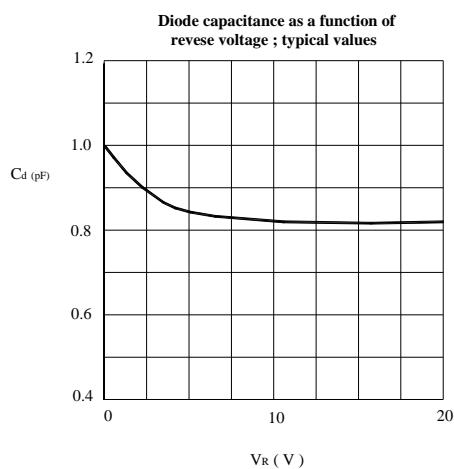




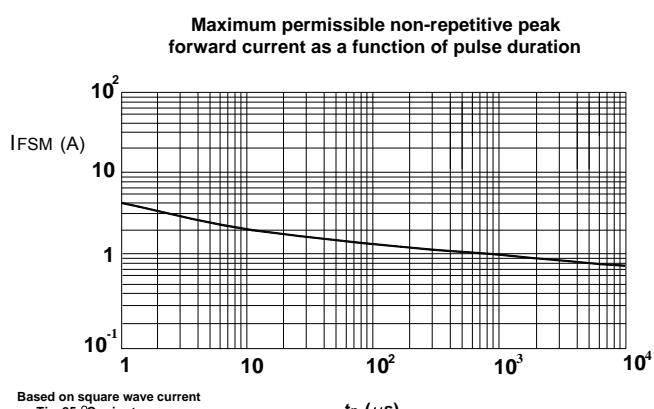
- (1)  $T_j = 175 \text{ } ^\circ\text{C}$ ; typical values
- (2)  $T_j = 25 \text{ } ^\circ\text{C}$ ; typical values
- (3)  $T_j = 25 \text{ } ^\circ\text{C}$ ; maximum values



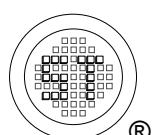
- (1)  $V_R = 75\text{V}$ ; maximum values
- (2)  $V_R = 75\text{V}$ ; typical values
- (3)  $V_R = 20\text{V}$ ; typical values



$f=1\text{MHz}; T_j=25 \text{ } ^\circ\text{C}$



Based on square wave current  
 $T_j = 25 \text{ } ^\circ\text{C}$  prior to surge



Dated : 15/06/2009